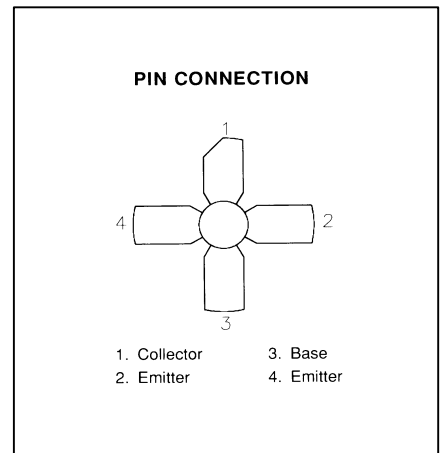
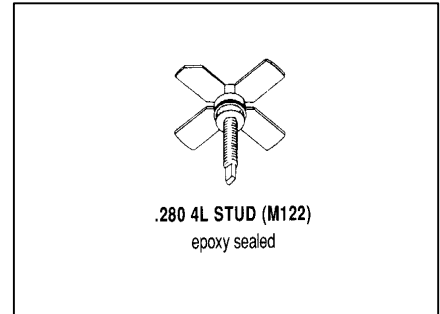


SD1144

## RF AND MICROWAVE TRANSISTORS UHF MOBILE APPLICATIONS

### Features

- **470 MHz**
- **12.5 VOLTS**
- **COMMON EMITTER**
- **COLLECTOR EFFICIENCY 60%**
- **P<sub>OUT</sub> = 2.0 W MIN.**
- **G<sub>P</sub> = 9 dB GAIN**



### DESCRIPTION:

The SD1144 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for UHF communications. This device utilizes improved metallization to achieve infinite VSWR at rated operating conditions.

### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
<b>V<sub>CBO</sub></b>	<b>Collector-Base Voltage</b>	<b>36</b>	<b>V</b>
<b>V<sub>CEO</sub></b>	<b>Collector-Emitter Voltage</b>	<b>16</b>	<b>V</b>
<b>V<sub>CES</sub></b>	<b>Collector-Emitter Voltage</b>	<b>36</b>	<b>V</b>
<b>V<sub>EBO</sub></b>	<b>Emitter-Base Voltage</b>	<b>4.0</b>	<b>V</b>
<b>I<sub>C</sub></b>	<b>Device Current</b>	<b>0.4</b>	<b>A</b>
<b>P<sub>DISS</sub></b>	<b>Power Dissipation</b>	<b>5.0</b>	<b>W</b>
<b>T<sub>J</sub></b>	<b>Junction Temperature</b>	<b>+200</b>	<b>°C</b>
<b>T<sub>STG</sub></b>	<b>Storage Temperature</b>	<b>-65 to +150</b>	<b>°C</b>

### THERMAL DATA

<b>R<sub>TH(j-c)</sub></b>	<b>Junction-Case Thermal Resistance</b>	<b>35</b>	<b>°C/W</b>
----------------------------	---	-----------	-------------

**ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)**
**STATIC**

Symbol	Test Conditions	Value			Units
		Min.	Typ.	Max.	
<b>BV<sub>CES</sub></b>	<b>I<sub>C</sub> = 50 mA    V<sub>BE</sub> = 0 V</b>	<b>36</b>			<b>V</b>
<b>BV<sub>CEO</sub></b>	<b>I<sub>C</sub> = 50 mA    I<sub>B</sub> = 0 mA</b>	<b>16</b>			<b>V</b>
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 1 mA    I<sub>C</sub> = 0 mA</b>	<b>4.0</b>			<b>V</b>
<b>I<sub>CB0</sub></b>	<b>V<sub>CB</sub> = 15 V    I<sub>E</sub> = 0 mA</b>			<b>1.0</b>	<b>mA</b>
<b>h<sub>FE</sub></b>	<b>V<sub>CE</sub> = 5 V    I<sub>C</sub> = 100 mA</b>	<b>20</b>			

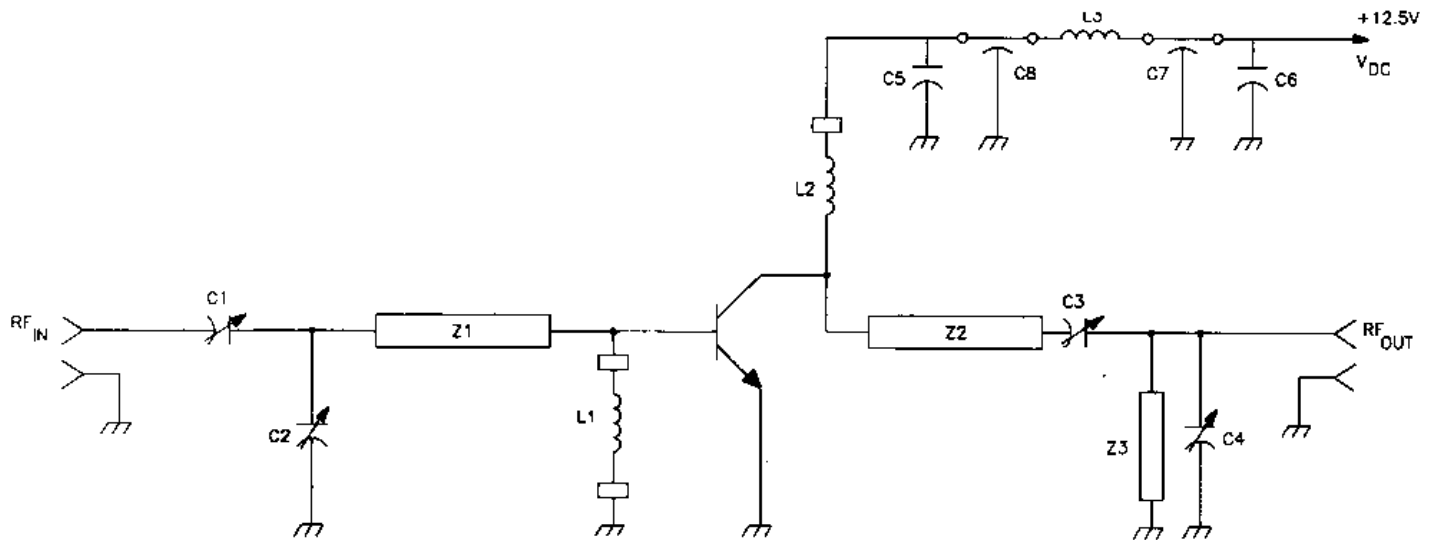
**DYNAMIC**

Symbol	Test Conditions	Value			Units
		Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 470 MHz    P<sub>IN</sub> = 0.25 W    V<sub>CE</sub> = 12.5 V</b>	<b>2.0</b>			<b>W</b>
<b>G<sub>P</sub></b>	<b>f = 470 MHz    P<sub>IN</sub> = 0.25 W    V<sub>CE</sub> = 12.5 V</b>	<b>9.0</b>			<b>dB</b>
<b>η<sub>C</sub></b>	<b>f = 175 MHz    P<sub>IN</sub> = 0.25 W    V<sub>CE</sub> = 12.5 V</b>	<b>60</b>			<b>%</b>
<b>C<sub>OB</sub></b>	<b>f = 1 MHz    V<sub>CB</sub> = 12.5 V</b>			<b>15</b>	<b>pF</b>

**IMPEDANCE DATA**

Freq.	Z <sub>IN</sub> (Ω)	Z <sub>L</sub> (Ω)
<b>470 MHz</b>	<b>2.24 + j 6.5</b>	<b>13.0 - j 8.65</b>

TEST CIRCUIT



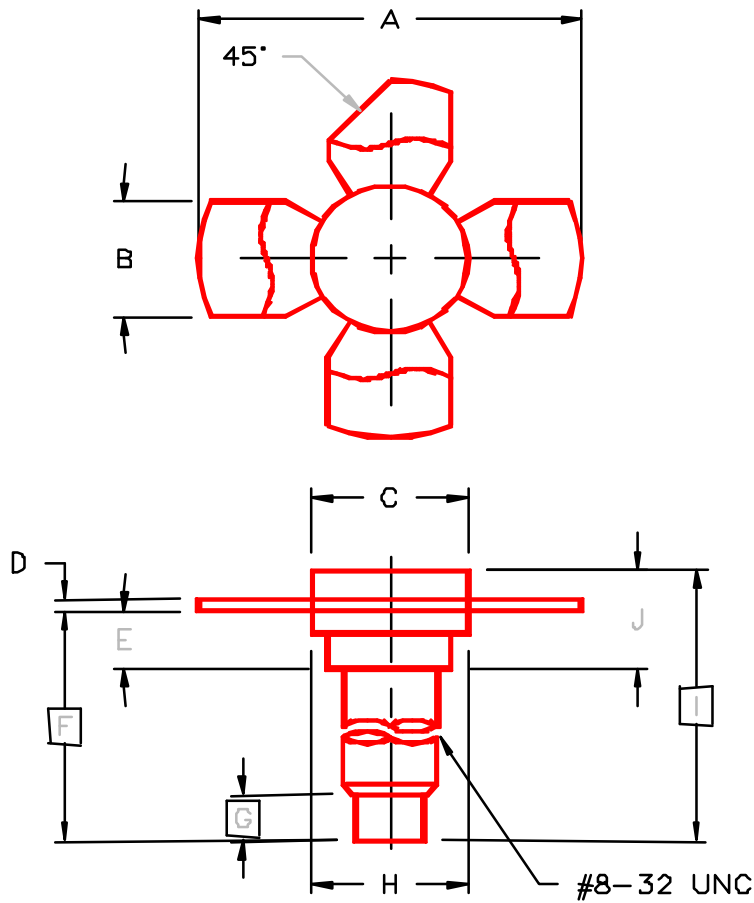
C1, C2 :  
 C3, C4 : 1.0 - 25pF, Arco 421  
 C5 : 1.0 $\mu$ F, 35V, Electrolytic  
 C6 : 4.7 $\mu$ F, 35V, Electrolytic  
 C7, C8 : 1000pF Feedthru

L1, L2 : 7 Turns #22 Enameled 0.175" I.D. with Ferroxcube  
 Ferrite Beads #56-590-65/3B  
 L3 : 2 Turns in Ferroxcube VK200/10-3B (RFC)

Board Material: Glass Teflon, 1/16" Duriod

PACKAGE MECHANICAL DATA

PACKAGE STYLE M122



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	1.010/25,65	1.055/26,80	I	.640/16,26	
B	.220/5,59	.230/5,84	J	.175/4,45	.217/5,51
C	.270/6,86	.285/7,24			
D	.003/0,08	.007/0,18			
E	.117/2,97	.137/3,48			
F	.572/14,53				
G	.130/3,30				
H	.275/6,99	.285/7,24			